



Part of 29

PTO/SB/08A (10-01)

Approved for use through 10/31/2002.OMB 0651-0031

U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	09/296,835	
			Filing Date	April 22, 1999	
			First Named Inventor	Ronald A. Weimer	
			Art Unit	2813	
			Examiner Name	E. Kielin	
Sheet	1	of	1	Attorney Docket Number	M4065.0319/P319

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
ER	A	6,063,698	05/16/00	Tseng et al.	
ER	B	6,197,668	03/06/01	Gardner, et al.	
ER	C	US-2001/0020725	09/13/01	Okuno, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
ER	D	LU, et al., "Leakage Current Comparison Between Ultra-Thin Ta ₂ O ₅ films and conventional gate dielectrics" IEEE Electron Device Letters 19(9), 9/1998, pp. 341-342		
ER	E	ALERS, et al., "Intermixing at the Tantalum Oxide/Silicon Interface in Gate Dielectric Structures" Applied Physics Letters 73(11), 14 September 1998, pp. 1517-1519		
ER	F	LUAN, et al., "Ultra-thin High Quality Ta ₂ O ₅ Dielectric Prepared by In-Situ Rapid Thermal Processing" Electron Devices Meeting, held 6-9 December 1998, IEDM '98 Technical Digest, pp. 609-612.		

Examiner Signature		Date Considered	6/14/03
--------------------	--	-----------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.